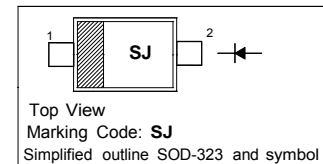


Surface Mount Schottky Barrier Diodes

Features

- Low forward voltage
- Low reverse capacitance

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit	
Peak Repetitive Reverse Voltage	V_{RRM}	SD101AWS SD101BWS SD101CWS	60 50 40	V
Reverse Voltage		SD101AWS SD101BWS SD101CWS	60 50 40	V
Forward Continuous Current		I_{FM}	15	mA
Power Dissipation	P_d	200	mW	
Non-Repetitive Peak Forward Surge Current	I_{FSM}	at $t = 1\text{ s}$	50	mA
		at $t = 10\ \mu\text{s}$	2	A
Operating and Storage Temperature Range	T_j, T_{stg}	- 65 to + 125	$^\circ\text{C}$	

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit	
Reverse Breakdown Voltage at $I_R = 10\ \mu\text{A}$	$V_{(BR)R}$	SD101AWS SD101BWS SD101CWS	60 50 40	V	
Forward Voltage at $I_F = 1\text{ mA}$		V_F	SD101AWS SD101BWS SD101CWS	- - -	0.41 0.4 0.39
at $I_F = 15\text{ mA}$			SD101AWS SD101BWS SD101CWS	- - -	1 0.95 0.9
Reverse Current at $V_R = 50\text{ V}$ at $V_R = 40\text{ V}$ at $V_R = 30\text{ V}$	I_R		SD101AWS SD101BWS SD101CWS	- - -	200 200 200
Total Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$		C_T	SD101AWS SD101BWS SD101CWS	- - -	2 2.1 2.2
Reverse Recovery Time at $I_F = I_R = 5\text{ mA}$, $I_{rr} = 0.1X I_R$, $R_L = 100\ \Omega$			t_{rr}	-	1

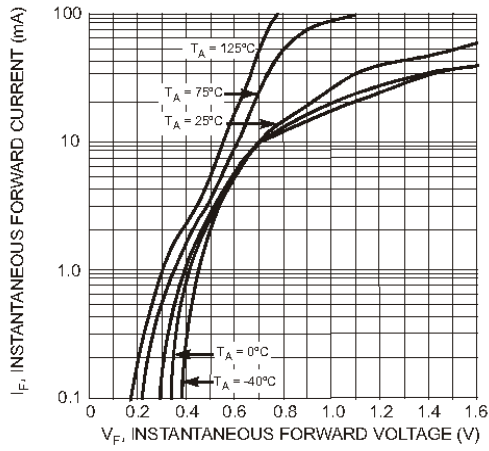


Fig. 1 Typical Forward Characteristics

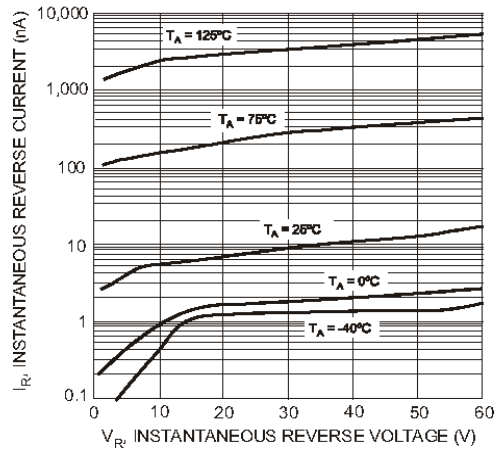


Fig. 2 Typical Reverse Characteristics

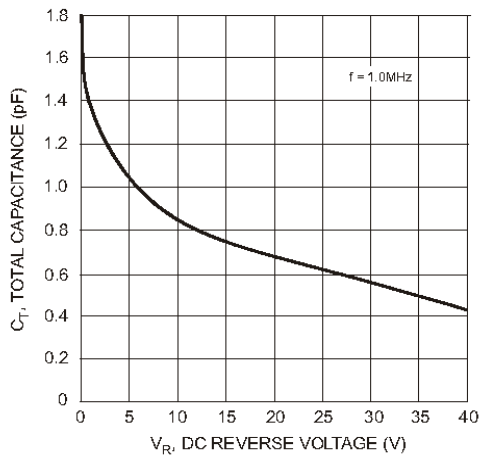


Fig. 3 Total Capacitance vs. Reverse Voltage

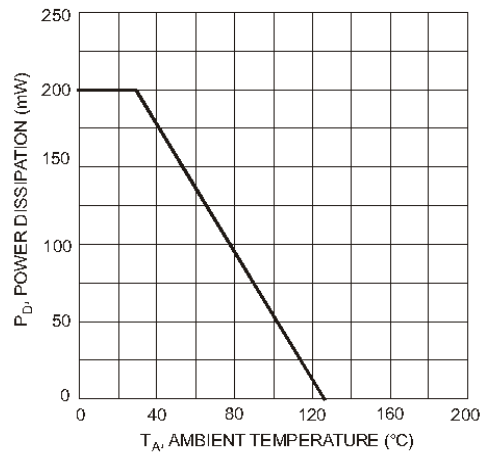


Fig. 4 Power Derating Curve



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SOD-323



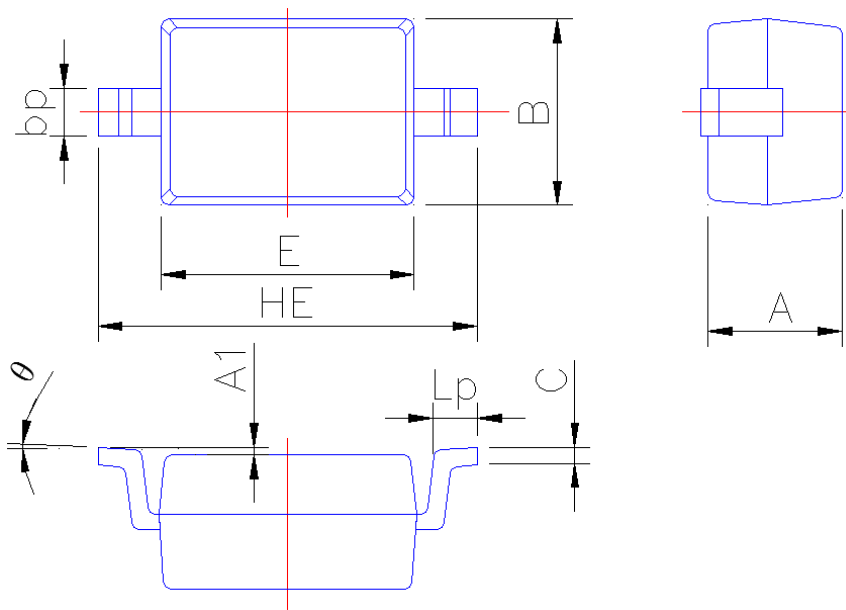
SD101AWS-SD101CWS

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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



Symbol	Dimension in Millimeters	
	Min	Max
A	0.95	1.15
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.40
C	0.09	0.150
E	1.60	1.80
HE	2.30	2.70
Lp	0.20	0.40
θ	0°	5°